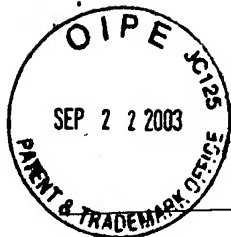


2818



PATENT

Case Docket No. IMEC279.001AUS  
Date: September 18, 2003

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s) : Van Houdt, et al.  
Appl. No. : 10/603,426  
Filed : June 24, 2003  
For : MULTIBIT NON-VOLATILE  
MEMORY AND METHOD  
Examiner : Unassigned  
Group Art Unit : 2818

I hereby certify that this correspondence and all marked attachments are being deposited with the United States Postal Service as first class mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on

September 18, 2003

(Date)

Mark M. Abumeri, Reg. No. 43,458

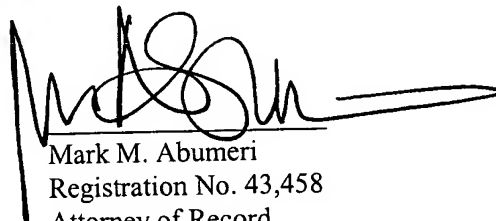
TRANSMITTAL LETTER

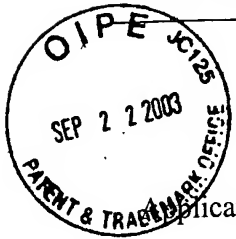
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Dear Sir:

Enclosed for filing in the above-identified application are:

- (X) An Information Disclosure Statement.
- (X) A PTO Form 1449 with twenty-two (22) references.
- (X) The Commissioner is hereby authorized to charge any additional fees which may be required, or credit any overpayment, to Account No. 11-1410.
- (X) Return prepaid postcard.

  
Mark M. Abumeri  
Registration No. 43,458  
Attorney of Record  
Customer No. 20,995  
(619) 235-8550

**INFORMATION DISCLOSURE STATEMENT**

Applicant : Van Houdt, et al.  
App. No. : 10/603,426  
Filed : June 24, 2003  
For : MULTIBIT NON-VOLATILE MEMORY  
AND METHOD  
Examiner : Unassigned  
Group Art Unit : 2818

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Dear Sir:

Enclosed is form PTO-1449 listing twenty-two (22) references that are also enclosed.

This Information Disclosure Statement is being filed with an RCE or within three months of the filing date of this application and no fee is required in accordance with 37 C.F.R. § 1.97(b)(1), (b)(2), or (b)(4).

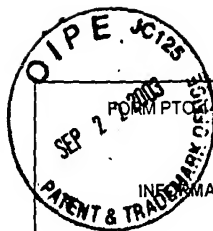
Respectfully submitted,

KNOBBE, MARTENS, OLSON & BEAR, LLP

Dated: September 18, 2003

By: 

Mark M. Abumeri  
Registration No. 43,458  
Attorney of Record  
Customer No. 20,995  
(619) 235-8550



SHEET 1 OF 2

FORM PTO 449 U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE INFORMATION DISCLOSURE STATEMENT BY APPLICANT  (USE SEVERAL SHEETS IF NECESSARY)	ATTY. DOCKET NO. IMEC279.001AUS	APPLICATION NO. 10/603,426
	APPLICANT Van Houdt, et al.	
	FILING DATE June 24, 2003	GROUP 2818

U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
	1	4,794,565	12/27/88	Wu, et al.			
	2	5,278,439	01/11/94	Ma, et al.			
	3	5,280,446	01/18/94	Ma, et al.			
	4	5,284,784	02/08/94	Manley			
	5	5,338,952	08/16/94	Yamauchi			
	6	5,394,360	02/28/95	Fukumoto			
	7	5,538,811	12/10/96	Van Houdt, et al.			
	8	5,841,697	11/24/98	Van Houdt, et al.			
	9	6,044,015	03/28/00	Van Houdt, et al.			
	10	6,366,500 B1	04/02/02	Ogura, et al.			
	11	6,580,120 B1	06/17/03	Haspeslagh			
	12	2002/0005545 A1	01/17/02	Widdershoven, et al.			

FOREIGN PATENT DOCUMENTS								
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
	13	EP 1 096 572 A1	05/02/01	EUROPE				

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)	
	14	Esquivel, et al., "High density contactless, self aligned EPROM cell array technology", IEDM Tech. Dig., pp. 592-595, (1986).
	15	Hayashi, et al., "Twin MONOS cell with dual control gates", IEEE, presented at the 2000 Symposium on VLSI Technology Digest of Technical Papers, pp. 122-123, (2000).
	16	<i>Micro lithography, Science and Technology</i> , Sheats, et al., Eds., Marcel Dekker, Inc., New York, New York, pp. 515-565 and 615-644, (1998).
	17	Miyawaki, et al., "A new erasing and row decoding scheme for low supply voltage operation 16-Mb/64-Mb flash memories", IEEE Journal of Solid-State Circuits, vol. 27, no. 4, pp. 583-588, (April 1992).
	18	Tanaka, et al., "A quick intelligent page-programming architecture and a shielded bitline sensing method for 3V-only NAND flash memory", IEEE Journal of Solid-State Circuits, vol. 29, no. 11, pp. 1366-1373, (November 1994).
	19	Van Houdt, et al., "A 5-volt-only fast-programming flash EEPROM cell with a double polysilicon split-gate structure", presented at the 11 <sup>th</sup> IEEE Non-volatile Semiconductor Memory Workshop, (February 1991).

EXAMINER	DATE CONSIDERED
*EXAMINER: INITIAL IF CITATION CONSIDERED, WHETHER OR NOT CITATION IS IN CONFORMANCE WITH MPEP 609; DRAW LINE THROUGH CITATION IF NOT IN CONFORMANCE AND NOT CONSIDERED, INCLUDE COPY OF THIS FORM WITH NEXT COMMUNICATION TO APPLICANT.	



FORM PTO 449 U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE INFORMATION DISCLOSURE STATEMENT BY APPLICANT (USE SEVERAL SHEETS IF NECESSARY)	ATTY. DOCKET NO. IMEC279.001AUS	APPLICATION NO. 10/603,426
APPLICANT Van Houdt, et al.		
FILING DATE June 24, 2003		GROUP 2818

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)	
20	Van Houdt, et al., "Analysis of the enhanced hot-electron injection in split-gate transistors useful for EEPROM applications, IEEE Transactions on Electron Devices, vol. 39, no. 5, pp. 1150-1156, (May 1992).	
21	Van Houdt, et al., "HIMOS-A high efficiency flash E2PROM cell for embedded memory applications", IEEE Transactions on Electron Devices, vol. 40, no. 12, pp. 2255-2263, (December 1993).	
22	Yamauchi, et al., "A 5V-only virtual ground flash cell with an auxiliary gate for high density and high speed application", IEDM Tech. Dig., p. 319-322, (1991).	

S:\DOCS\IMMA\IMMA-7547.DOC/cfg/091703

EXAMINER	DATE CONSIDERED
*EXAMINER: INITIAL IF CITATION CONSIDERED, WHETHER OR NOT CITATION IS IN CONFORMANCE WITH MPEP 609; DRAW LINE THROUGH CITATION IF NOT IN CONFORMANCE AND NOT CONSIDERED, INCLUDE COPY OF THIS FORM WITH NEXT COMMUNICATION TO APPLICANT.	